

isc Silicon NPN Power Transistor

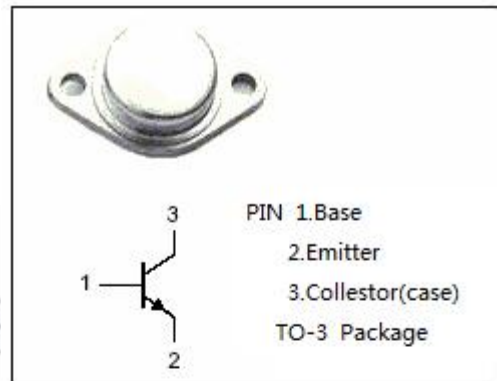
2SD1278

DESCRIPTION

- High Breakdown Voltage-
: $V_{CBO} = 1200V$ (Min)
- High Reliability
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

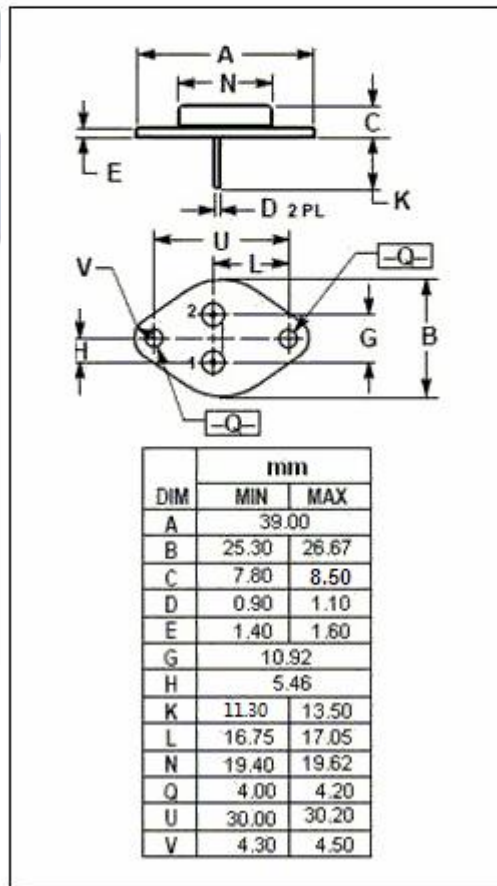
APPLICATIONS

- Designed for high voltage power switching TV horizontal deflection output applications.



ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1200	V
V_{CEO}	Collector-Emitter Voltage	600	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current- Continuous	8	A
I_{CP}	Collector Current-Peak	10	A
P_C	Collector Power Dissipation @ $T_c = 25^\circ C$	100	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc Silicon NPN Power Transistor**2SD1278****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	5			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; R _{BE} = ∞	600			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 8A; I _B = 1.5A			10	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 8A; I _B = 1.5A			1.5	V
I _{CES}	Collector Cutoff Current	V _{CE} = 1200V ; R _{BE} = 0			0.5	mA
h _{FE-1}	DC Current Gain	I _C = 1A ; V _{CE} = 5V	10		40	
h _{FE-2}	DC Current Gain	I _C = 5A ; V _{CE} = 5V	4			